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Version with Markings to Show Changes Made

SPECIFICATIONS:

Page 3, line 11, change the paragraph as:

FIG. 3 shows the cross section along line [AA'] 1-1' and line [BB'] 2-2' of FIG. 1.

Page 5, line 21 to page 6, line 2, change the paragraph as:

FIG. 3 shows the cross section along line [AA'] 1-1' and line [BB'] 2-2' of FIG.

1. Along line [AA'] 1-1' of FIG. 1 is the steps of fabricating the thin film transistor, the data line and the scan line. Along line [BB'] 2-2' is the steps of fabricating the pixel electrodes 101 and the common electrode 102.

Page 6, lines 3-10, change the paragraph as:

Referring to FIG. 3, the cross section along line [AA'] 1-1' of FIG. 1 illustrates in detail every layer of the structure above the substrate. A metallic layer of the scan signal line 301 is first formed above the glass substrate 303. Then, the glass substrate 303 is covered with an insulator layer 304 and an island-like region 305 is formed to provide an active layer for the thin film transistor. The thin film transistor comprises at least a gate, a drain, and a source. The gate terminal of the thin film transistor connects to the scan signal line 301, the drain terminal connects to the data signal line 307 and the source terminal connects to the pixel electrodes 306.

Page 6, line 22 to page 7, line 4, change the paragraph as:

Along line [BB'] 2-2' of FIG. 1 is the steps of forming the layer of pixel electrodes. A layer of herringbone-shaped pixel electrodes 309 is fabricated above the

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